

IN THE CLAIMS

This is a complete and current listing of the claims, marked with status identifiers in parentheses. The following listing of claims will replace all prior versions and listings of claims in the application.

1. (Currently Amended) A semiconductor polishing composition comprising:

fumed silica, the semiconductor polishing composition being an aqueous dispersion solution of fumed silica,

wherein an increase rate of average particle diameter of fumed silica after a shake test for 10 days is 10% or less.

2. (Original) The semiconductor polishing composition of claim 1, wherein a content of the fumed silica is in a range of 10 to 30% by weight based on a total amount of the composition.

3. (Currently Amended) The semiconductor polishing composition of claim ~~1 or 2~~, wherein the average particle diameter of the fumed silica is in a range of 70 to 110 nm.

4. (Currently Amended) The semiconductor polishing composition of ~~any one of claims 1 to 3~~, wherein the semiconductor polishing composition is prepared by adding an

acidic fumed silica dispersion solution to an alkali aqueous solution.

5. (Original) The semiconductor polishing composition of claim 4, wherein a pH of the alkali aqueous solution is in a range of 12 to 14.

6. (New) The semiconductor polishing composition of claim 2, wherein the average particle diameter of the fumed silica is in a range of 70 to 110 nm.

7. (New) The semiconductor polishing composition of claim 2, wherein the semiconductor polishing composition is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.

8. (New) The semiconductor polishing composition of claim 3, wherein the semiconductor polishing composition is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.

9. (New) The semiconductor polishing composition of claim 6, wherein the semiconductor polishing composition is prepared by adding an acidic fumed silica dispersion solution to an alkali aqueous solution.

10. (New) The semiconductor polishing composition of claim 7, wherein a pH of the alkali aqueous solution is in a range of 12 to 14.

11. (New) The semiconductor polishing composition of claim 8, wherein a pH of the alkali aqueous solution is in a range of 12 to 14.

12. (New) The semiconductor polishing composition of claim 9, wherein a pH of the alkali aqueous solution is in a range of 12 to 14.